AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, wherein a metal film is formed by applying an adhesive film, comprising an adhesive layer formed on one surface of a base film comprising at least one film layer having a gas transmission rate of not more than ~~5.0 cc/m^2·day·atm~~ 49.35 ml/m^2·day/MPa, to a circuit-formed surface of a semiconductor wafer (a non-metal-film-formed surface).

2. (Currently Amended) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the base film comprises a metal film layer or a metal oxide film layer, and at least one film layer having a gas transmission rate of not more than ~~5.0 cc/m^2·day·atm~~ 49.35 ml/ m^2·day/MPa.

3. (Currently Amended) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the base film comprises at least one film layer having a gas transmission rate of not more than ~~1.0 cc/m^2·day·atm~~ 9.87 ml/ m^2·day/MPa and water absorptance of not more than 1.0 weight %.

4. (Currently Amended) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to ~~any one of claims 1 to 3~~ claim 1, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

5. (Currently Amended) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to ~~any one of claims 1 to 3~~ claim 1, wherein the adhesive layer has a storage elastic modulus of not less than 1×10^5 Pa at 150°C.

6. (Currently Amended) An adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, comprising an adhesive layer formed on one surface of a base film comprising at least one film layer having a gas transmission rate of not more than ~~5.0 cc/m^2·day·atm~~ 49.35 ml/ m^2·day/MPa.

7. (Currently Amended) An adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, comprising an adhesive layer formed on one surface of a base film comprising at least one film layer having a gas transmission rate of not more than ~~1.0 cc/m^2·day·atm~~ 9.87 ml/ m^2·day/MPa and water absorptance of not more than 1.0 weight %.

8. (New) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the base film further

comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

9. (New) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 3, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

10. (New) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the adhesive layer has a storage elastic modulus of not less than 1×10^5 Pa at 150°C.

11. (New) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 3, wherein the adhesive layer has a storage elastic modulus of not less than 1×10^5 Pa at 150°C.